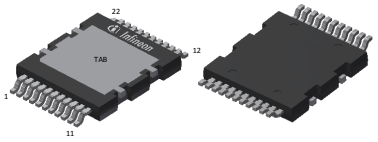
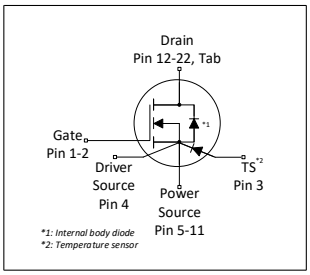
MOSFET

600V CoolMOS™ SJ S7A Power Device

PG-HDSOP-22



CoolMOS™ S7A reduce $R_{DS(on)}$ values for an HV SJ MOSFET, with a distinctive increase in energy efficiency. CoolMOS™ S7A is optimized for "static switching" and high current applications. The embedded temperature sensor increases junction temperature sensing accuracy and robustness while keeping an easy and seamless implementation.



Features

- CoolMOS™ S7A technology enables lowest $R_{DS(on)}$ and high pulse current capability in the smallest footprint
- Optimized price performance in low-frequency switching applications
- Seamless diagnostics at lowest system cost
- Temperature sense feature for protection and optimized thermal device utilization

Benefits

- Minimized conduction losses (reduced heat sink size)
- Increased system performance
- Lower BOM or/and TCO over a prolonged lifetime
- Reduction of external sensing elements

Compared to electromechanical devices:
- Faster switching times; More reliability and longer system lifetime
- Shock & Vibration resistance; No contact arcing or bouncing

Potential applications

- Solid state relays and circuit breakers
- Line rectification in high power/performance applications

Product validation

Qualified according to AEC Q101

Please note: The source and sense source pins are not exchangeable. Their exchange might lead to malfunction. For paralleling 4pin MOSFET devices the placement of the gate resistor is generally recommended to be on the Driver Source instead of the Gate. For production part approval process (PPAP) release we propose to share application related information during an early design phase to avoid delays in PPAP release. Please contact Infineon sales office.

Table 1 Key Performance Parameters

Parameter	Value	Unit
$R_{DS(on),max}$	10	mΩ
$Q_{g,typ}$	318	nC
V_{SD}	0.82	V
Pulsed I_{SD}, I_{DS}	796	A
ESD class (HBM)	2	JEDEC AEC Q101

Type / Ordering Code	Package	Marking	Related Links
IPDQ60T010S7A	PG-HDSOP-22	60T010S7	see Appendix A

Table of Contents

1 Maximum ratings

at T_j = 25°C, unless otherwise specified

Table 2 Maximum MOSFET ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain current rating[1)]	I_D	- -	- -	174 50	A	T_C=25°C T_C=140°C
Pulsed drain current[2)]	$I_{D,pulse}$	-	-	796	A	T_C=25°C
Avalanche energy, single pulse	E_{AS}	-	-	612	mJ	I_D=6.3A; V_{DD}=50V; see table 12
Avalanche current, single pulse	I_{AS}	-	-	6.3	A	-
MOSFET dv/dt ruggedness[3)]	dv/dt	-	-	20	V/ns	V_{DS}= 0V to 300V
Gate source voltage (static)	V_{GS}	-20	-	20	V	static
Gate source voltage (dynamic)	V_{GS}	-30	-	30	V	AC (f>1 Hz)
Power dissipation	P_{tot}	-	-	694	W	T_C=25°C
Storage temperature	T_{stg}	-55	-	150	°C	-
Operating junction temperature[1)]	T_j	-40	-	150	°C	-
Extended operating junction temperature	T_j	150	-	175	°C	≤50 h in the application lifetime
Mounting torque	-	-	-	n.a.	Ncm	-
Diode forward current rating	I_S	-	-	50	A	T_C=140°C Current is limited by $T_{j\,max}$ = 150°C; Lower case temp does increase current capability
Diode pulse current[2)]	$I_{S,pulse}$	-	-	796	A	T_C=25°C
Reverse diode dv/dt[4)]	dv/dt	-	-	5	V/ns	V_{DS}=0 to 300V, I_{SD}<=50A, T_j=25°C see table 10
Maximum diode commutation speed	di_f/dt	-	-	800	A/µs	V_{DS}=0 to 300V, I_{SD}<=50A, T_j=25°C see table 10
Insulation withstand voltage	V_{ISO}	-	-	n.a.	V	-

[1)] Please consider the App Note: 600 V CoolMOS™ S7 with Temperature Sense for high delta T_J usage
[2)] Pulse width t_p limited by $T_{j,max}$
[3)] The dv/dt has to be limited by appropriate gate resistor
[4)] Identical low side and high side switch

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	0.18	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	62	°C/W	device on PCB, minimal footprint
Thermal resistance, junction - ambient for SMD version	R_{thJA}	-	45	55	°C/W	Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70µm thickness) copper area. Tap exposed to air. PCB is vertical without air stream cooling.
Soldering temperature, reflow soldering allowed	T_{sold}	-	-	260	°C	reflow MSL1

3 Electrical characteristics

at T_j=25°C, unless otherwise specified

Table 4 Static characteristics

The CoolMOS™ mentioned in this datasheet shall not be operated in linear mode.
For any questions in this regard, please contact Infineon sales office.
For applications with applied blocking voltage >400V, it is required that the customer evaluates the impact of cosmic radiation effect in early design phase and contacts the Infineon sales office for the necessary technical support by Infineon

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	600	-	-	V	V_{GS}=0V, I_D=1mA
Gate threshold voltage	$V_{(GS)th}$	3.5	4.0	4.5	V	V_{DS}=V_{GS}, I_D=3.06mA
Zero gate voltage drain current	I_{DSS}	- -	- 80	8 -	µA	V_{DS}=600V, V_{GS}=0V, T_j=25°C V_{DS}=600V, V_{GS}=0V, T_j=150°C
Gate-source leakage current	I_{GSS}	-	-	100	nA	V_{GS}=20V, V_{DS}=0V
Drain-source on-state resistance	$R_{DS(on)}$	- -	0.009 0.022	0.010 -	Ω	V_{GS}=12V, I_D=50A, T_j=25°C V_{GS}=12V, I_D=50A, T_j=150°C
Gate resistance	R_G	-	0.45	-	Ω	f=1MHz, open drain

Table 5 Dynamic characteristics

External parasitic elements (PCB layout) influence switching behavior significantly.
Stray inductances and coupling capacitances must be minimized.
For layout recommendations please use provided application notes or contact Infineon sales office.

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	11986	-	pF	V_{GS}=0V, V_{DS}=300V, f=250kHz
Output capacitance	C_{oss}	-	188	-	pF	V_{GS}=0V, V_{DS}=300V, f=250kHz
Effective output capacitance, energy related[1)]	$C_{o(er)}$	-	643	-	pF	V_{GS}=0V, V_{DS}=0 to 300V
Effective output capacitance, time related[2)]	$C_{o(tr)}$	-	5714	-	pF	I_D=constant, V_{GS}=0V, V_{DS}=0 to 300V
Output charge	Q_{oss}	-	1714	-	nC	V_{GS}=0V, V_{DS}=0 to 300V
Turn-on delay time	$t_{d(on)}$	-	32	-	ns	V_{DD}=300V, V_{GS}=13V, I_D=50A, R_G=3Ω; see table 11
Rise time	t_r	-	12	-	ns	V_{DD}=300V, V_{GS}=13V, I_D=50A, R_G=3Ω; see table 11
Turn-off delay time	$t_{d(off)}$	-	170	-	ns	V_{DD}=300V, V_{GS}=13V, I_D=50A, R_G=3Ω; see table 11
Fall time	t_f	-	9	-	ns	V_{DD}=300V, V_{GS}=13V, I_D=50A, R_G=3Ω; see table 11

[1)] $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 300V
[2)] $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 300V

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	69	-	nC	V_{DD}=300V, I_D=50A, V_{GS}=0 to 12V
Gate to drain charge	Q_{gd}	-	105	-	nC	V_{DD}=300V, I_D=50A, V_{GS}=0 to 12V
Gate charge total	Q_g	-	318	-	nC	V_{DD}=300V, I_D=50A, V_{GS}=0 to 12V
Gate plateau voltage	$V_{plateau}$	-	5.7	-	V	V_{DD}=300V, I_D=50A, V_{GS}=0 to 12V

Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.82	-	V	V_{GS}=0V, I_F=50A, T_j=25°C
Reverse recovery time	t_{rr}	-	600	-	ns	V_R=300V, I_F=50A, di_F/dt=100A/µs; see table 10
Reverse recovery charge	Q_{rr}	-	17	-	µC	V_R=300V, I_F=50A, di_F/dt=100A/µs; see table 10
Peak reverse recovery current	I_{rrm}	-	55	-	A	V_R=300V, I_F=50A, di_F/dt=100A/µs; see table 10

4 Temperature Sensor parameters

at T_j=25°C, unless otherwise specified

Table 8 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Repetitive Peak Reverse Voltage	V_{RRM}	-	-	15	V	I_R = 100 µA
Sensor forward current	I_F	-	-	5	mA	-
Repetitive peak forward current	I_{F_pulse}	-	-	25	mA	t_{pulse} = 1 ms, T_{period} = 10 ms
Non-repetitive peak forward current	I_{FSM}	- - -	- - -	1.5 0.2 0.1	A	T_C = 25°C, t_{pulse} = 1 µs T_C = 25°C, t_{pulse} = 1 ms T_C = 25°C, t_{pulse} = 1 s
Junction Temperature	T_j	-	-	185	°C	t < 50h, Sensor only

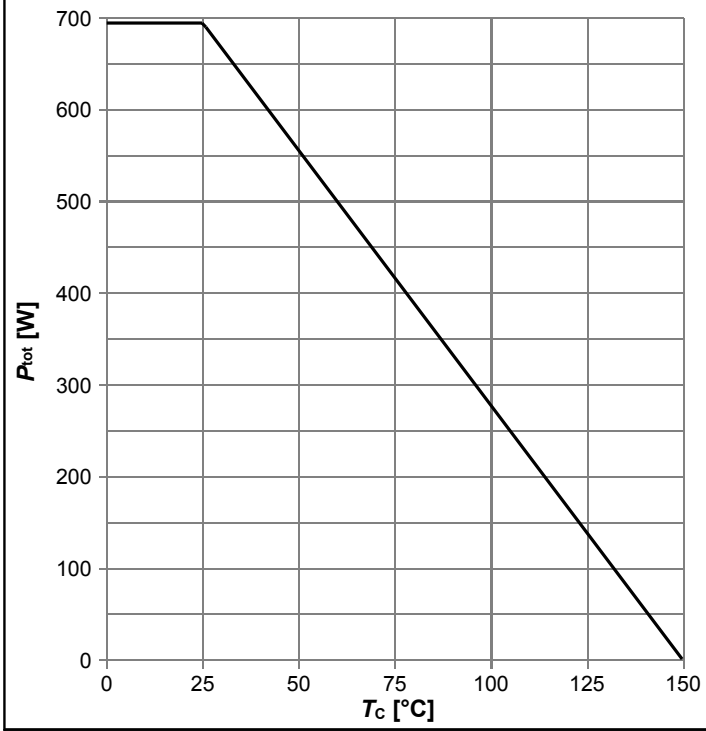
Table 9 Electrical characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Sensor forward voltage[1)]	V_{F_25}	1.5601 - - 2.0665	1.6019 1.8103 1.9806 2.0966	1.6436 - - 2.1266	V	T_j = 25°C, I_F = 10 µA T_j = 25°C, I_F = 50 µA T_j = 25°C, I_F = 200 µA T_j = 25°C, I_F = 500 µA
Sensor forward voltage temperature coefficient	TC	- - - -	5.9644 5.5880 5.2287 5.0135	- - - -	mV/K	25°C ≤ T_j ≤ 175°C, I_F = 10 µA 25°C ≤ T_j ≤ 175°C, I_F = 50 µA 25°C ≤ T_j ≤ 175°C, I_F = 200 µA 25°C ≤ T_j ≤ 175°C, I_F = 500 µA
Sensor forward voltage	V_{F_175}	0.6655 - - 1.3144	0.7072 0.9721 1.1963 1.3445	0.7490 - - 1.3746	V	T_j = 175°C, I_F = 10 µA T_j = 175°C, I_F = 50 µA T_j = 175°C, I_F = 200 µA T_j = 175°C, I_F = 500 µA
Reverse leakage current	I_R	- -	- -	1 20	µA	V_R = 10V, T_j = 25°C V_R = 10V, T_j = 175°C
Sensor G Capacitance	C_{GTS}	-	4.2	-	pF	f = 1 MHz, I_F = 50 µA
Sensor Capacitance	C_{STS}	-	4.8	-	pF	f = 1 MHz, I_F = 50 µA
Anode-Drain Capacitance	C_{DTS}	-	0.5	-	pF	f = 1 MHz, V_{DS} = 0 V

[1)] Specified by Design and not tested

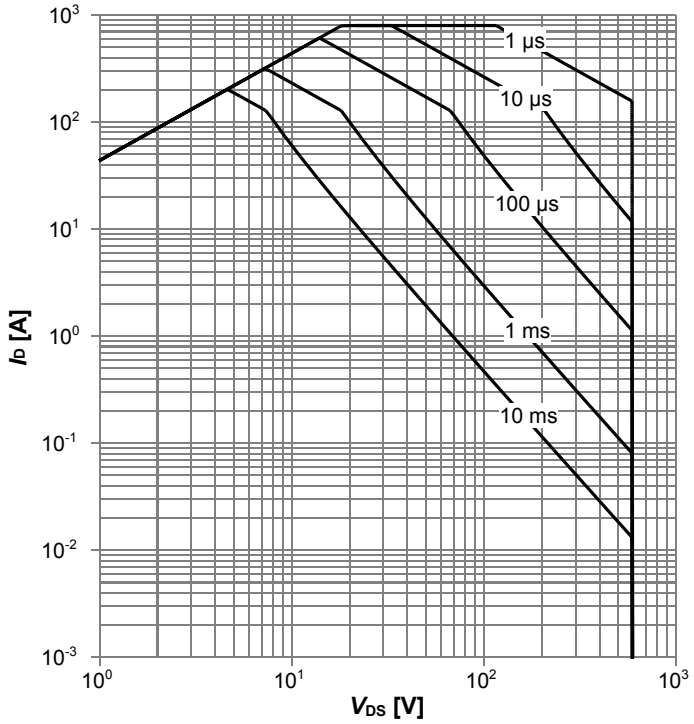
5 Electrical characteristics diagrams

Diagram 1: Power dissipation



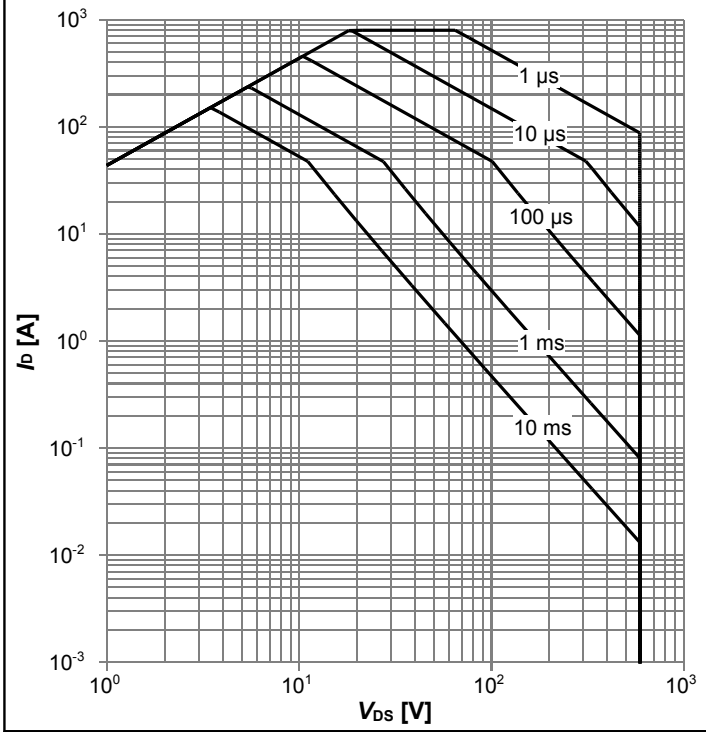
$P_{tot}=f(T_C)$

Diagram 2: Safe operating area



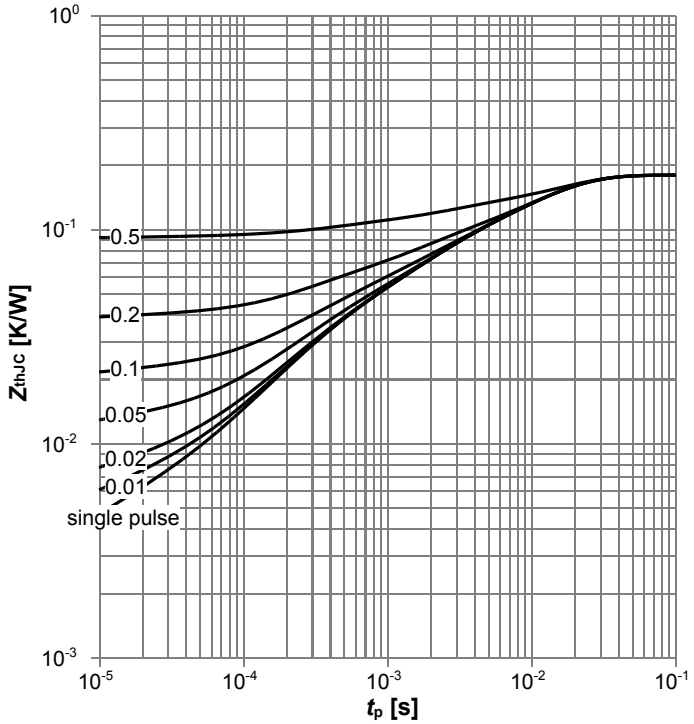
$I_D=f(V_{DS})$; T_C=25 °C; D=0; parameter: t_p

Diagram 3: Safe operating area



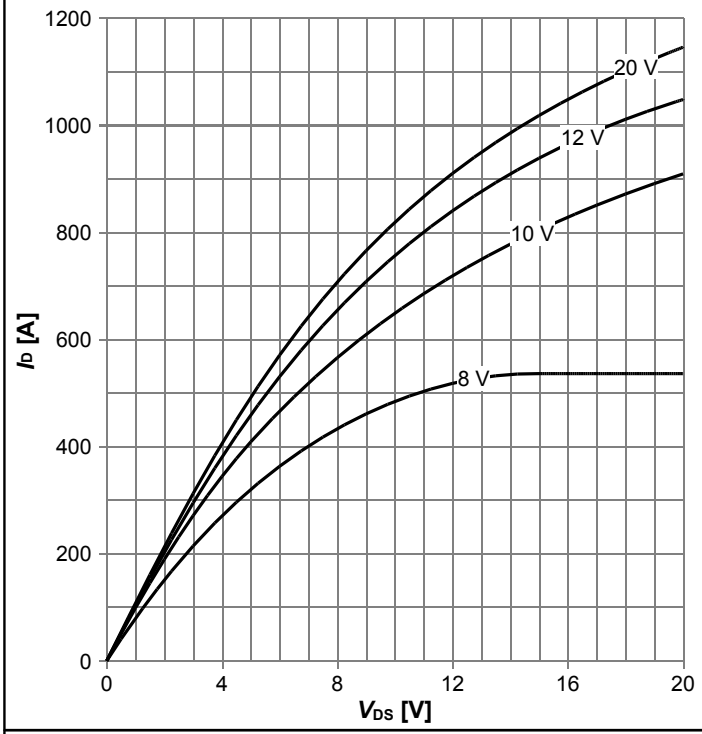
$I_D=f(V_{DS})$; T_C=80 °C; D=0; parameter: t_p

Diagram 4: Max. transient thermal impedance



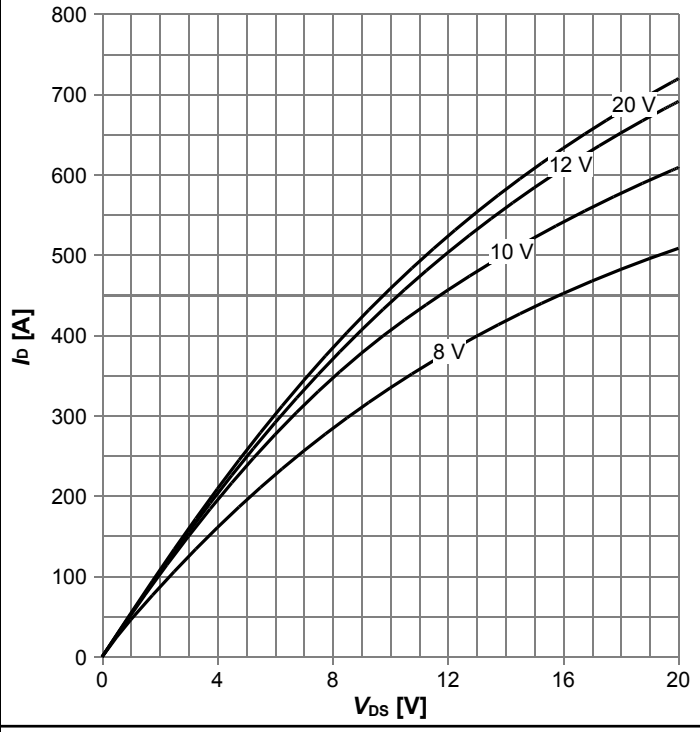
$Z_{thJC}=f(t_P)$; parameter: $D=t_p/T$

Diagram 5: Typ. output characteristics



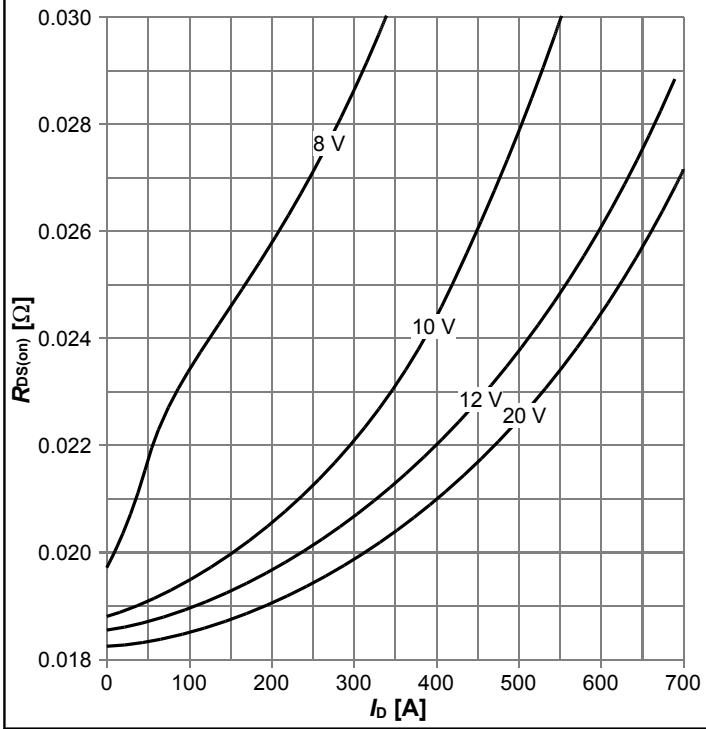
$I_D=f(V_{DS})$; $T_j=25$ °C; parameter: V_{GS}

Diagram 6: Typ. output characteristics



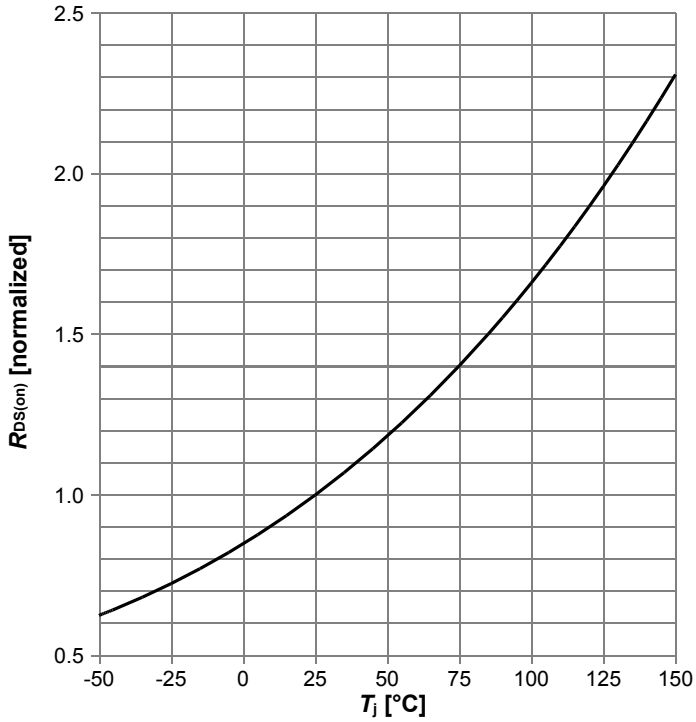
$I_D=f(V_{DS})$; $T_j=125$ °C; parameter: V_{GS}

Diagram 7: Typ. drain-source on-state resistance



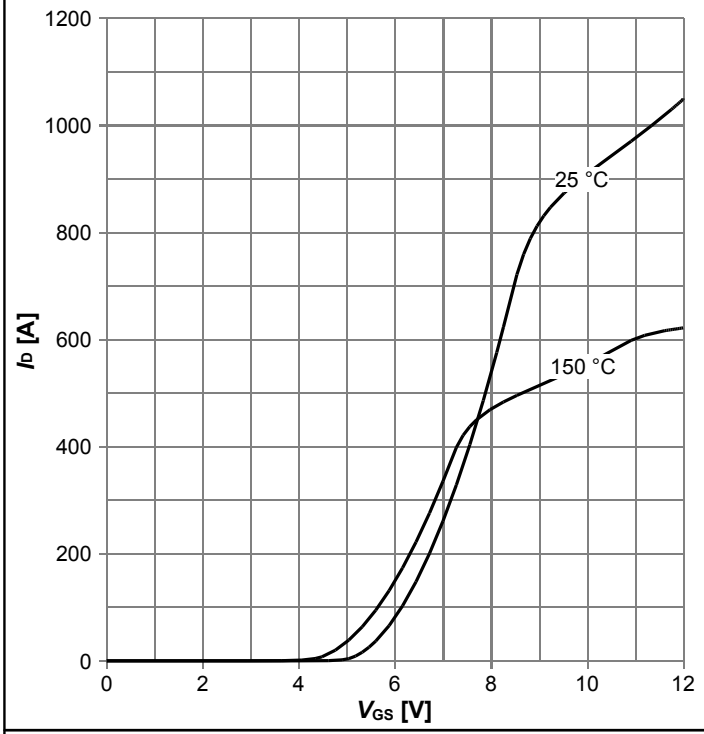
$R_{DS(on)}=f(I_D)$; $T_j=125$ °C; parameter: V_{GS}

Diagram 8: Drain-source on-state resistance



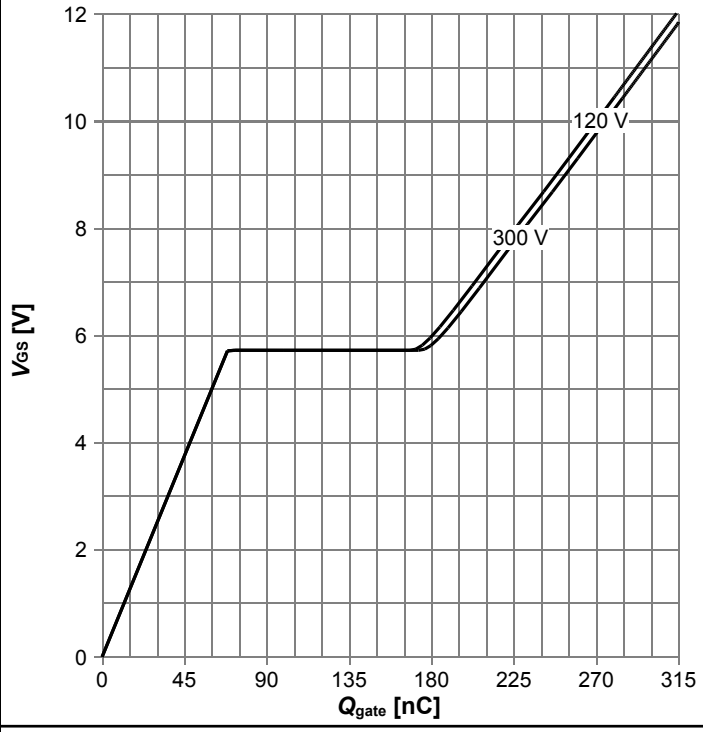
$R_{DS(on)}=f(T_j)$; $I_D=50$ A; $V_{GS}=12$ V

Diagram 9: Typ. transfer characteristics



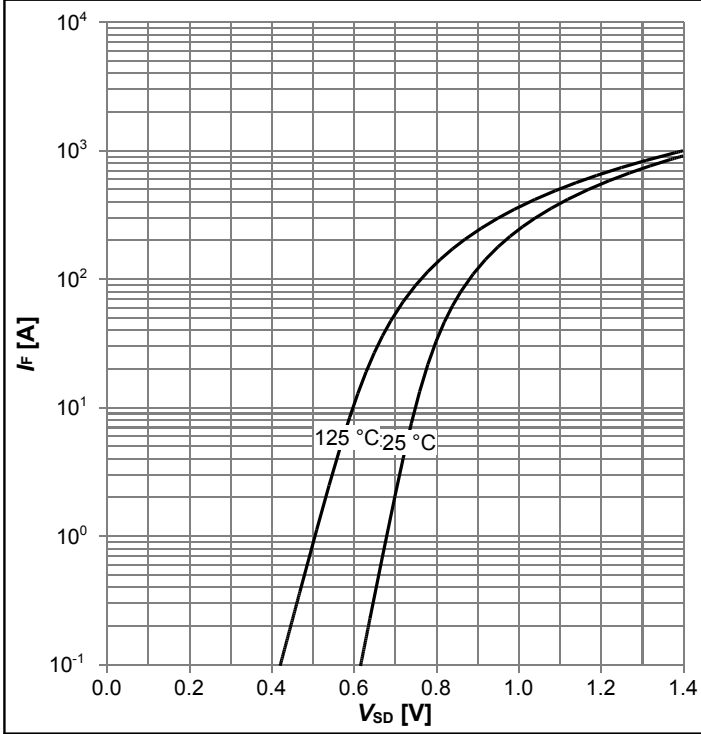
I_D=f(V_{GS}); V_{DS}=20V; parameter: T_j

Diagram 10: Typ. gate charge



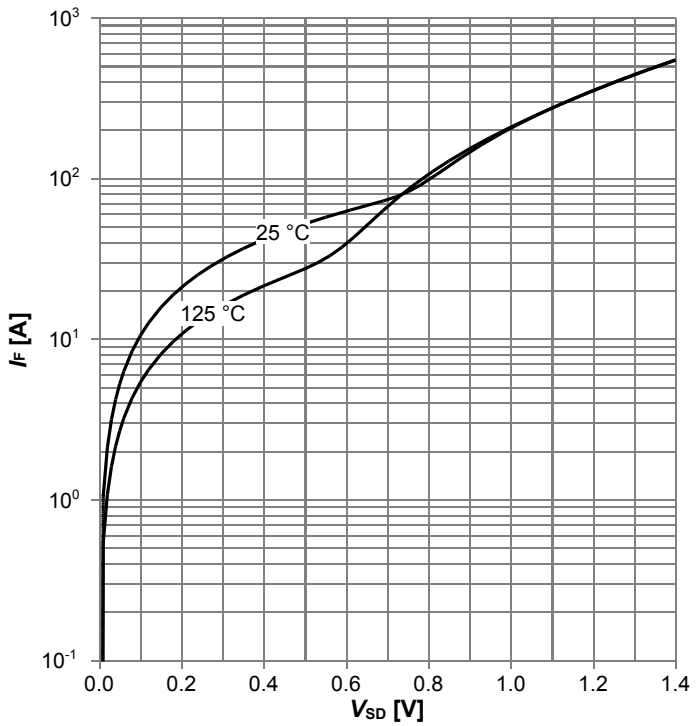
V_{GS}=f(Q_{gate}); I_D=50 A pulsed; parameter: V_{DD}

Diagram 11: Forward characteristics of reverse diode



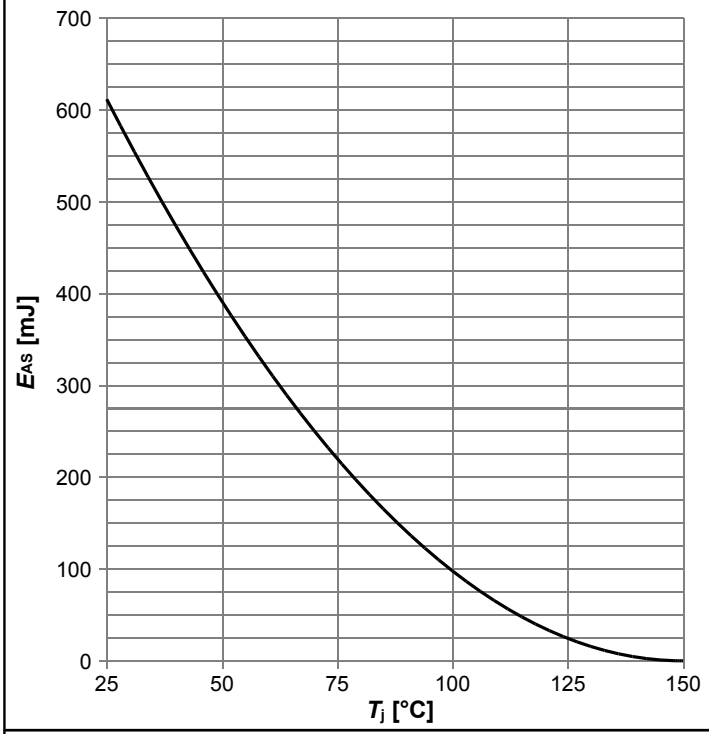
I_F=f(V_{SD}); V_{GS}=0 V; parameter: T_j

Diagram 12: Forward characteristics of reverse diode



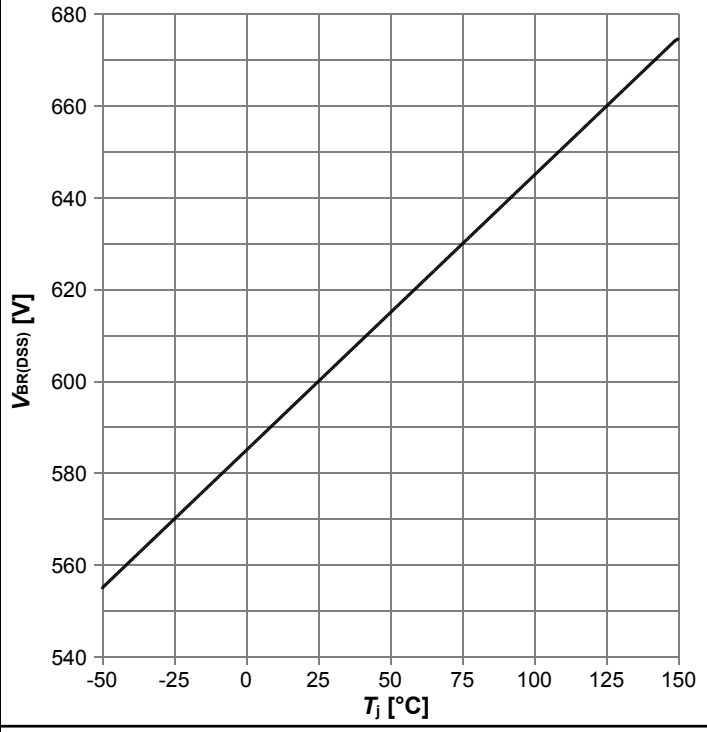
I_F=f(V_{SD}); V_{GS}=12 V; parameter: T_j

Diagram 13: Avalanche energy



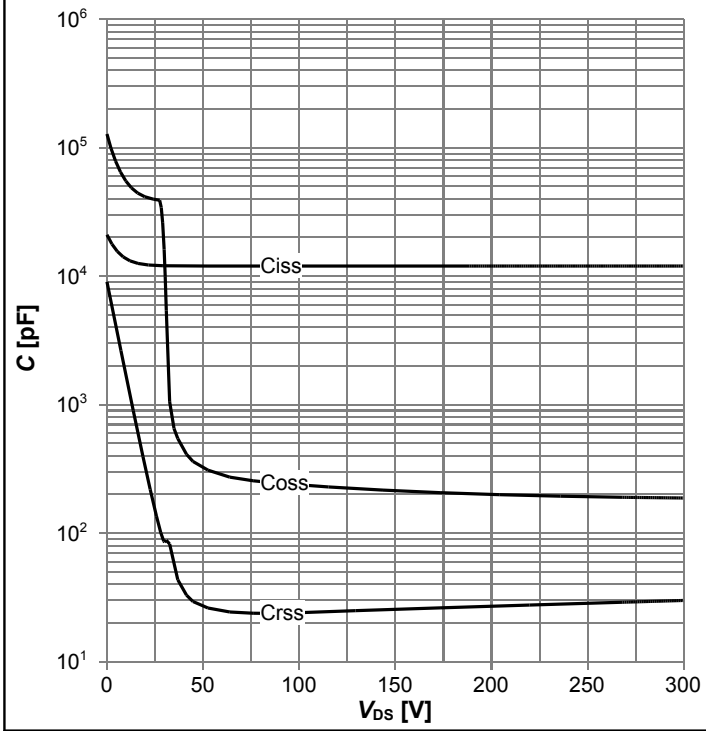
$E_{AS}=f(T_j)$; I_D=6.3 A; V_{DD}=50 V

Diagram 14: Drain-source breakdown voltage



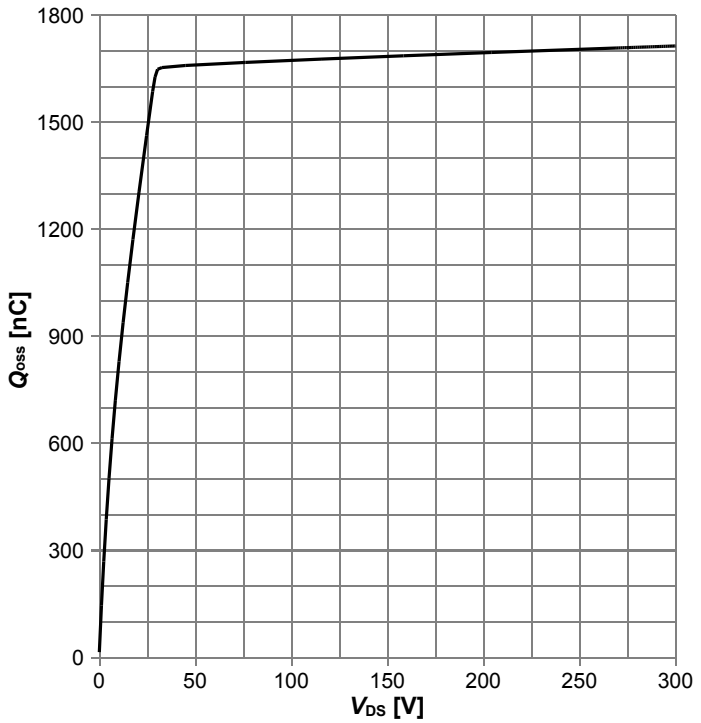
$V_{BR(DSS)}=f(T_j)$; I_D=1 mA

Diagram 15: Typ. capacitances



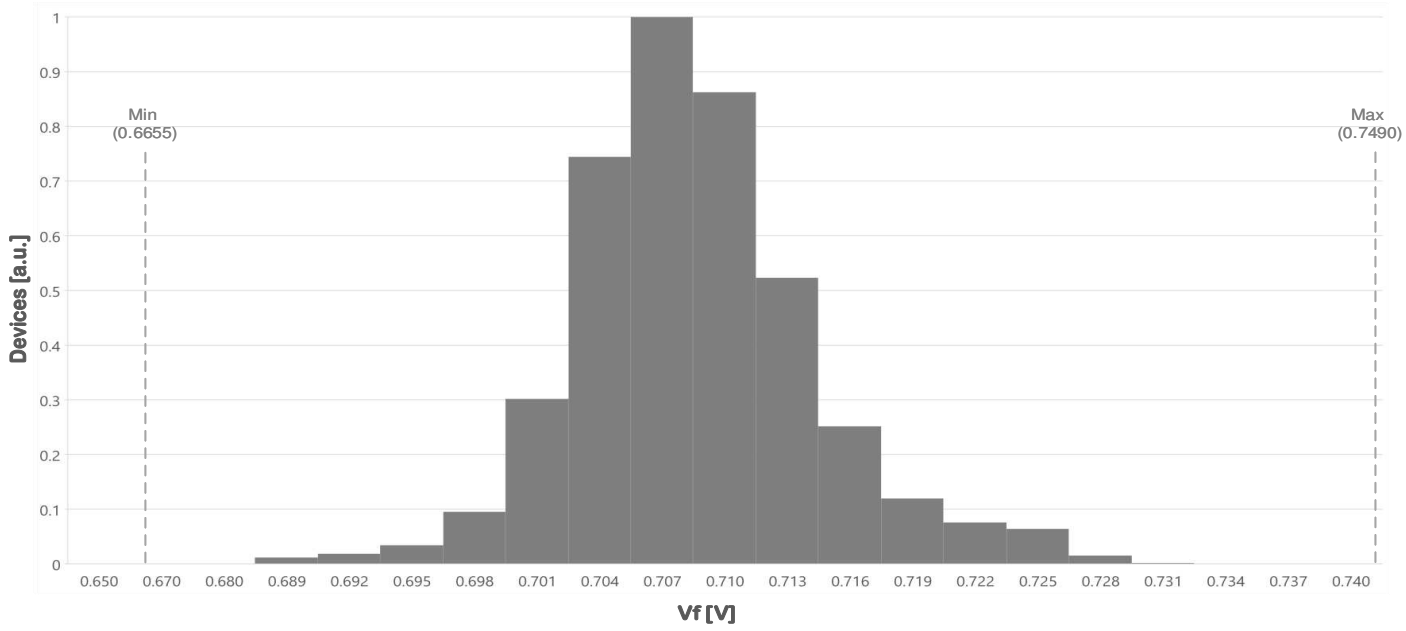
$C=f(V_{DS})$; V_{GS}=0 V; f=250 kHz

Diagram 17: Typ. Qoss output charge



$Q_{oss}=f(V_{DS})$; V_{GS}=0 V

Diagram: Distribution of typical temperature sensor signal



T_{j_set}=175 °C; I_{F_set} = 10 µA

6 Test Circuits

Table 10 Diode characteristics

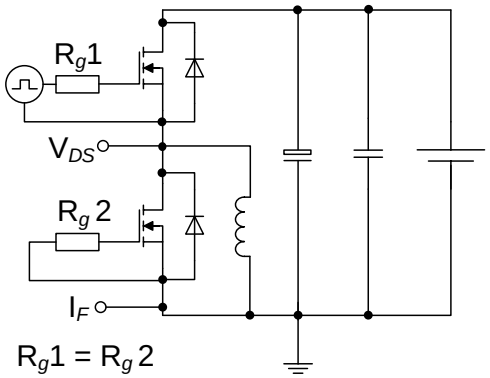
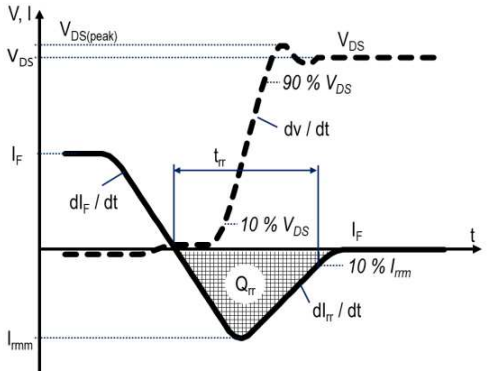
Test circuit for diode characteristics	Diode recovery waveform
	

Table 11 Switching times (ss)

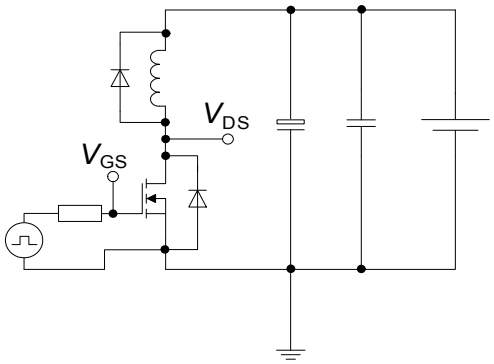
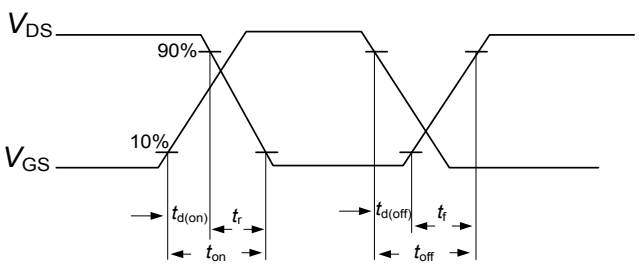
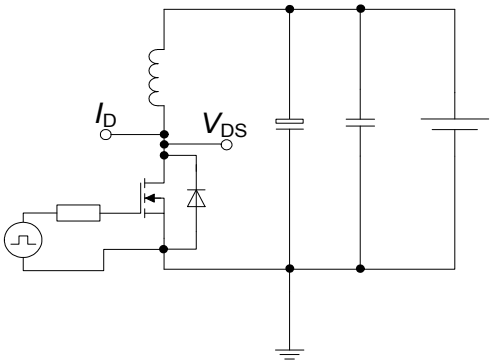
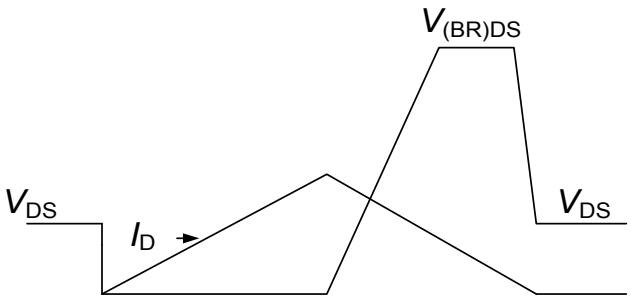
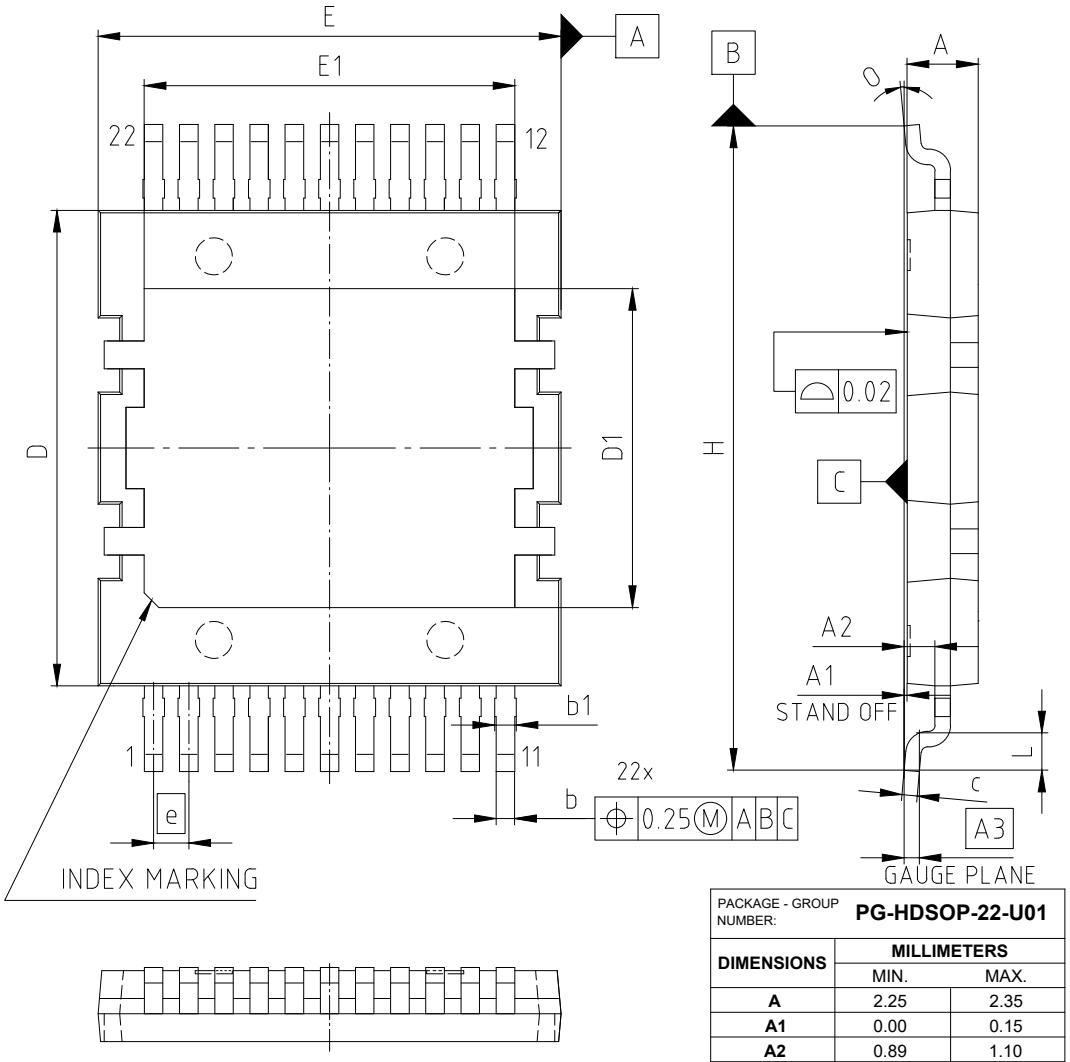
Switching times test circuit for inductive load	Switching times waveform
	

Table 12 Unclamped inductive load (ss)

Unclamped inductive load test circuit	Unclamped inductive waveform
	

7 Package Outlines



PACKAGE - GROUP NUMBER:	PG-HDSOP-22-U01	
DIMENSIONS	**MILLIMETERS**	
	MIN.	MAX.
A	2.25	2.35
A1	0.00	0.15
A2	0.89	1.10
A3	0.5	
b	0.50	0.70
b1	0.50	0.90
c	0.46	0.58
D	15.30	15.50
D1	10.23	10.43
E	14.90	15.10
E1	11.91	12.11
e	1.14	
N	22	
H	20.86	21.06
L	1.20	1.40
O	0°	8°

NOTES:

1. ALL DIMENSIONS REFER TO JEDEC STANDARD TO-252 AND DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS.
2. ALL METAL SUFACES ARE TIN PLATED, EXCEPT AREA OF CUT.

Figure 1 Outline PG-HDSOP-22, dimensions in mm

8 Appendix A

Table 13 Related Links

- **IFX CoolMOS™ S7TA Webpage:** www.infineon.com
- **IFX CoolMOS™ S7TA application note:** www.infineon.com
- **IFX CoolMOS™ S7TA simulation model:** www.infineon.com
- **IFX Design tools:** www.infineon.com

Revision History

IPDQ60T010S7A

Revision: 2024-03-18, Rev. 2.0

Previous Revision		
Revision	Date	Subjects (major changes since last revision)
2.0	2024-03-18	Release of final version

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81726 München, Germany
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